

AMENDMENTS TO THE DRAWINGS

In accordance with U.S. Patent and Trademark Office practice, proposed drawing changes as REPLACEMENT SHEETS are attached, wherein Applicant proposes to amend the drawings in the above-identified application as follows:

Please amend Figure 1 by replacing, in item (b), the rightmost "12b" with -- 12a --.

Please amend Figure 2 by replacing, within S102, "DIZE" with -- SIZE --.

No new matter has been added. Approval is earnestly requested.

REMARKS

This is in full and timely response the non-final Office Action mailed on July 25, 2006. Reexamination in light of the following remarks is respectfully requested.

Claims 21-30 are currently pending in this application, with claim 12 being independent.

No new matter has been added.

Drawings

Figures 1 and 2 have been amended to correct typographical errors found therein.

Rejections under 35 U.S.C. §102

Paragraph 3 of the Office Action indicates a rejection of claims 1-7 and 15-20 under 35 U.S.C. §102 as allegedly being anticipated by U.S. Patent Application No. 2003/013742 to Irie et al. (Irie-CIP Application).

This rejection is traversed at least for the following reasons.

While not conceding the propriety of this rejection and to advance the prosecution of the above-identified application, claims 1-7 and 15-20 have been canceled.

Withdrawal of this rejection is respectfully requested.

Newly added claims

Claims 21-30 - Claims 22-30 are dependent upon claim 21. Claim 21 is drawn to an exposure method comprising the steps of:

providing a V-line reflective mask, a mask pattern for said V-line reflective mask consisting of V-line pattern forming elements;

providing an H-line reflective mask, a mask pattern for said H-line reflective mask consisting of H-line pattern forming elements;

irradiating a light onto one of said V-line and H-line reflective masks, said light reflected from said one of said V-line and H-line reflective masks being projected onto a wafer;

rotating said wafer and another of said V-line and H-line reflective masks; and

irradiating said light onto said another of said V-line and H-line reflective masks, said light reflected from said another of said V-line and H-line reflective masks being projected onto said wafer.

Irie-CIP Application - The Irie-CIP Application arguably teaches an exposure method and exposure apparatus.

However, the above-identified application is entitled to the benefit of Japanese Patent Application No. 2002-189086 having a priority date of June 28, 2002.

The filing date for the Irie-CIP Application of November 19, 2002 is *later* than the priority date of Japanese Patent Application No. 2002-189086. An English language translation of Japanese Patent Application No. 2002-189086 *has been previously filed* on July 3, 2006. M.P.E.P. §201.15. Please take this English language translation into account in the examination of this application.

The Irie-CIP Application appears to claim the benefit of application No. 09/827,946 (Irie-Parent Application). The filing date for the Irie-Parent Application of April 9, 2001 is earlier than the priority date for the Japanese Patent Application No. 2002-189086 of June 28, 2002.

Accordingly, the review will be based upon the Irie-Parent Application.

Irie-Parent Application - The Irie-Parent Application has published as U.S. Patent Application Publication No. 2001/0055733. Irie arguably teaches an exposure method and exposure apparatus. Irie arguably teaches the presence of a master pattern 27 of the working reticle 34 (Irie at Figure 6, paragraph [0110]). The Irie-Parent Application arguably teaches the presence of a parent pattern 36 (Irie at Figure 6, paragraph [0112]).

The Irie-Parent Application arguably teaches that by producing N number of master reticles R1 to RN at one time, it is possible to produce the number of necessary working reticles 34 by repeatedly using them, so the time for producing the master reticles R1 to RN does not become a large burden (Irie at Figure 6, paragraph [0115]).

Nevertheless, the Irie-Parent Application fails to disclose, teach, or suggest the step of rotating the wafer and another of said V-line and H-line reflective masks.

Moreover, the Irie-Parent Application fails to disclose, teach, or suggest the step of irradiating a light onto one of the V-line and H-line reflective masks, wherein the light reflected from one of said V-line and H-line reflective masks is projected onto a wafer.

In addition, the Irie-Parent Application fails to disclose, teach, or suggest the step of irradiating the light onto another of said V-line and H-line reflective masks, wherein the light reflected from said another of said V-line and H-line reflective masks is projected onto the wafer.

In this regard, the Irie-Parent Application fails to disclose, teach, or suggest the master reticles R1 to RN as being adapted to reflect light onto a substrate 4 (Irie at Figure 1). Instead, the

Irie-Parent Application arguably teaches that a reticle, however, is generally prepared by depositing chrome on a transparent glass substrate (Irie at paragraph [0136]).

Allowance of the claims is respectfully requested.

Conclusion

For the foregoing reasons, all the claims now pending in the present application are allowable at least for the reasons provided hereinabove and for the additional features that they recite. Thus, the present application is in condition for allowance. Accordingly, favorable reexamination and reconsideration of the application in light of the amendments and remarks is courteously solicited.

If the Examiner has any comments or suggestions that could place this application in even better form, the Examiner is requested to telephone Brian K. Dutton, Reg. No. 47,255, at 202-955-8753.

If any fee is required or any overpayment made, the Commissioner is hereby authorized to charge the fee or credit the overpayment to Deposit Account # 18-0013.

Dated: December 27, 2006

Respectfully submitted,

By _____

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Attachments: Replacement Sheet

Application No. 10/603,689

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REPLACEMENT SHEET